



# LAPD-2-06-17-CHIP



## TECHNICAL DATA

### Photodiode Chip die

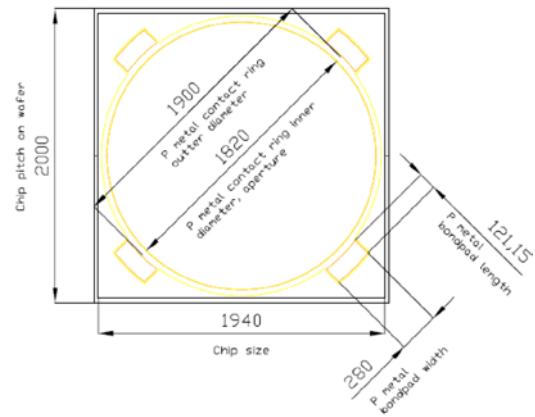
### InGaAs

LAPD-2-06-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is Ø 2 mm respectively.



### Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	$U_R$	20	V
Reverse Current	$I_R$	20	mA
Forward current	$I_F$	10	mA
Operating Temperature	$T_{opr}$	-20 ... +85	°C
Storage Temperature	$T_{stg}$	-40 ... +85	°C



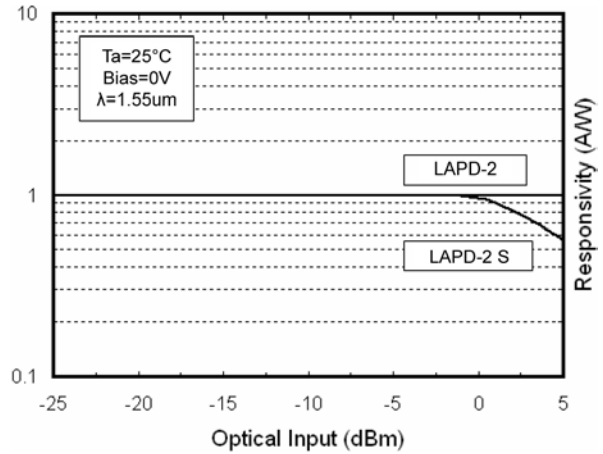
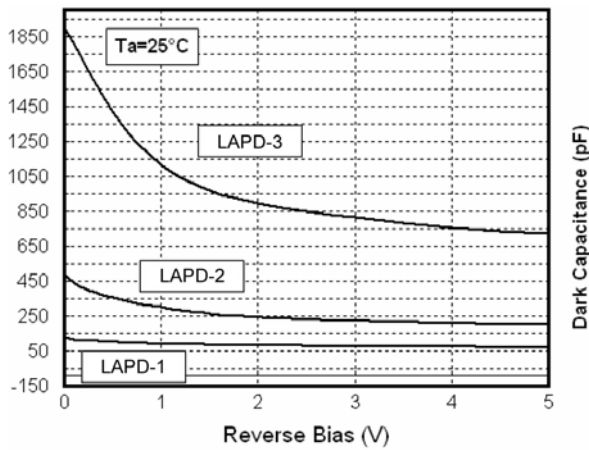
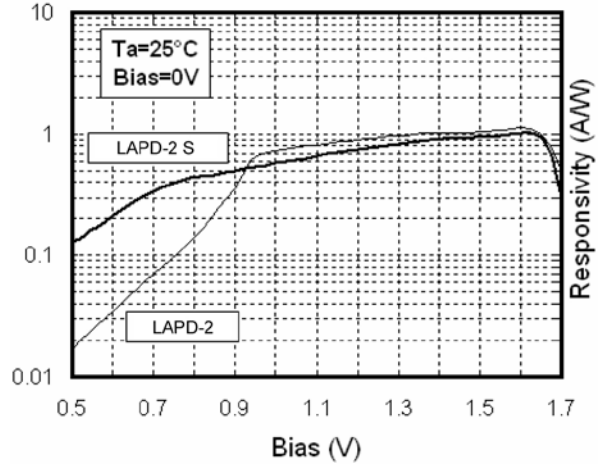
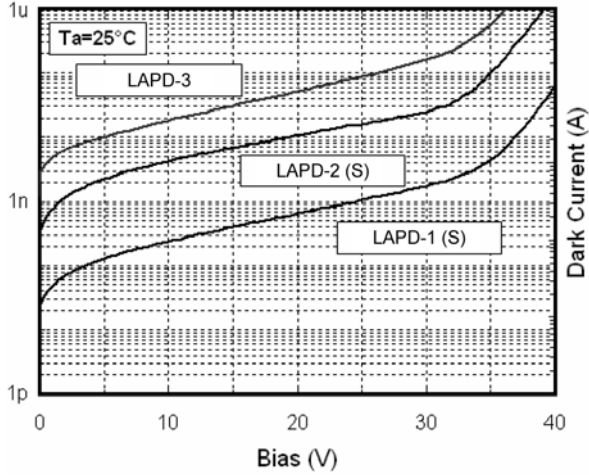
### Specifications

Item	Min.	Typ.	Max.	Unit	
Wavelength Range	0.6 .. 1.7			µm	
Active Area	Ø 2			mm	
Saturation Power	1550 nm	-	-3	-	dBm
Specific Detectivity ( $D^*$ )	1550 nm	2.5	5	-	$10^{12}$ Jones
Responsibility (0 V)	650 nm	0.20	0.30	-	A/W
	850 nm	0.40	0.50	-	
	1310 nm	0.80	0.90	-	
	1550 nm	0.85	0.95	-	
Capacitance	0 V	-	500	800	pF
	-5 V	-	250	400	
Dark Current	-5 V	-	10	40	nA
Shunt Resistance	6	25	-	-	MΩ
Chip Size	1940 x 1940			µm	
Chip Thickness	300			µm	

**Packing:** Chips on adhesive film



## Typical Performance Curves



LAPD-2 Spatial Response  
 $T_a = 25^\circ\text{C}$ ,  $\text{Bias} = 0\text{V}$ ,  $\lambda = 1550\text{nm}$

